

### **SS9013**

# **1W Output Amplifier of Potable Radios in Class B Push-pull Operation.**

- • High total power dissipation. (P<sub>T</sub>=625mW)
- • High Collector Current. (I<sub>C</sub>=500mA)
- Complementary to SS9012
- • Excellent h<sub>FE</sub> linearity.



1. Emitter 2. Base 3. Collector

# **NPN Epitaxial Silicon Transistor**

# Absolute Maximum Ratings $T_a=25$ °C unless otherwise noted

| Symbol           | Parameter                 | Ratings   | Units |  |
|------------------|---------------------------|-----------|-------|--|
| $V_{CBO}$        | Collector-Base Voltage    | 40        | V     |  |
| V <sub>CEO</sub> | Collector-Emitter Voltage | 20        | V     |  |
| V <sub>EBO</sub> | Emitter-Base Voltage      | 5         | V     |  |
| I <sub>C</sub>   | Collector Current         | 500       | Α     |  |
| P <sub>C</sub>   | Collector Dissipation     | 625       | W     |  |
| TJ               | Junction Temperature      | 150       | °C    |  |
| T <sub>STG</sub> | Storage Temperature       | -55 ~ 150 | °C    |  |

### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

| Symbol                | Parameter                            | Test Condition                              | Min. | Тур. | Max. | Units |
|-----------------------|--------------------------------------|---|------|------|------|-------|
| BV <sub>CBO</sub>     | Collector-Base Breakdown Voltage     | $I_C = 100 \mu A, I_E = 0$                  | 40   |      |      | V     |
| BV <sub>CEO</sub>     | Collector-Emitter Breakdown Voltage  | $I_C = 1 \text{mA}, I_B = 0$                | 20   |      |      | V     |
| BV <sub>EBO</sub>     | Emitter-Base Breakdown Voltage       | $I_E = 100 \mu A, I_C = 0$                  | 5    |      |      | V     |
| I <sub>CBO</sub>      | Collector Cut-off Current            | $V_{CB} = 25V, I_{E} = 0$                   |      |      | 100  | nA    |
| I <sub>EBO</sub>      | Emitter Cut-off Current              | $V_{EB} = 3V$ , $I_C = 0$                   |      |      | 100  | nA    |
| h <sub>FE1</sub>      | DC Current Gain                      | $V_{CE} = 1V$ , $I_{C} = 50mA$              | 64   | 120  | 202  |       |
| $h_{FE2}$             |                                      | $V_{CE} = 1V$ , $I_{C} = 500$ mA            | 40   | 120  |      |       |
| V <sub>CE</sub> (sat) | Collector-Emitter Saturation Voltage | $I_C = 500 \text{mA}, I_B = 50 \text{mA}$   |      | 0.16 | 0.6  | V     |
| V <sub>BE</sub> (sat) | Base-Emitter Saturation Voltage      | I <sub>C</sub> =500mA, I <sub>B</sub> =50mA |      | 0.91 | 1.2  | V     |
| V <sub>BE</sub> (on)  | Base-Emitter On Voltage              | $V_{CE} = 1V$ , $I_{C} = 10mA$              | 0.6  | 0.67 | 0.7  | V     |

# **h**<sub>FE</sub> Classification

| Classification   | D       | E        | F        | G         | Н         |
|------------------|---------|----------|----------|-----------|-----------|
| h <sub>FE1</sub> | 64 ~ 91 | 78 ~ 112 | 96 ~ 135 | 112 ~ 166 | 144 ~ 202 |

# **Typical Characteristics**

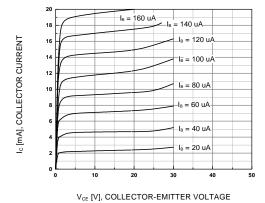


Figure 1. Static Characteristic

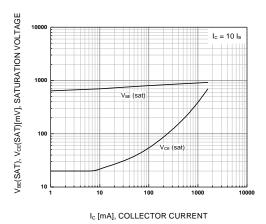


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

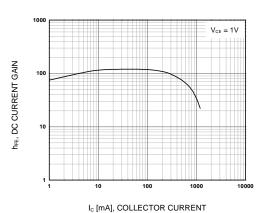


Figure 2. DC current Gain

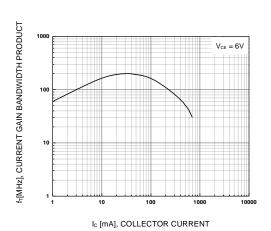
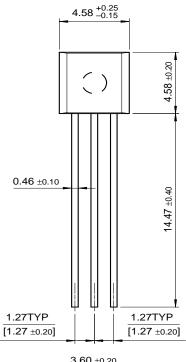
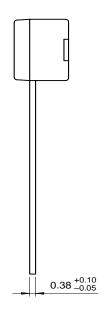


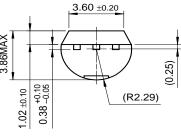
Figure 4. Current Gain Bandwidth Product

# **Package Demensions**

TO-92







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